METHOD OF FORMING A GATE STACK STRUCTURE

ABSTRACT

A method of forming an integrated circuit structure on a substrate, the substrate includes a primary region and a secondary region. A first layer of a first material of a first thickness is formed over the substrate. A portion of the first layer is removed over the primary region to expose the substrate. The structure is exposed to an oxidizing medium. This forms a second layer, for example, of an oxide material primary region of the substrate. The second layer has a second thickness. Additionally, at least a portion of said first layer is converted to a third layer, for example, of an oxynitride material. The third layer has a third thickness.

Figure 7